

Vishay Siliconix

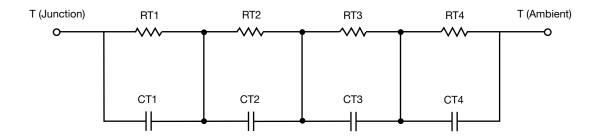
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



-C VALUES FOR TANK CONFIGURATION						
THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RT1	12.4192	556.8432m	N/A			
RT2	2.8985	738.1177m	N/A			
RT3	10.1424	329.2093m	N/A			
RT4	55.2157	1.3758	N/A			
	THERMAL CAPAC	TANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CT1	20.7904m	709.1664u	N/A			
CT2	3.7774m	8.0816m	N/A			
CT3	259.7058m	67.3476m	N/A			
CT4	1.2841	10.4083m	N/A			

Note

N/A indicates not applicable

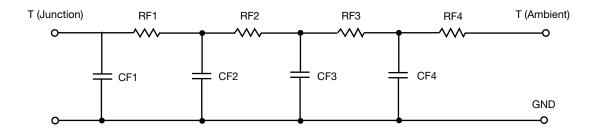
This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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R-C THERMAL MODEL FOR FILTER CONFIGURATION



R-C VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	3.2140	992.6589m	N/A		
RF2	16.5468	859.7187m	N/A		
RF3	14.6795	699.4999m	N/A		
RF4	46.3047	450.4512m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	2.0826m	757.8560u	N/A		
CF2	18.3645m	4.9808m	N/A		
CF3	425.0845m	2.0207m	N/A		
CF4	1.0408	7.7182m	N/A		

Note

N/A indicates not applicable





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